

SPECIFICATION OF LED CHIP C660-30V [RED]

1) Commodity Type and Physical Characteristics.

- | | | | |
|----------------------|--------------------|-------------------|------------------|
| 1. Material | GaAlAs/GaAlAs(DDH) | | |
| 2. Electrode | Top Side | N (cathode)side | :Au Alloy/Al Pad |
| | Bottom Side | P (anode)side | :Au Alloy |
| 3. Electrode Pattern | Fig.1 | | |
| 4. Chip Size | Fig.2 | | |
| 5. Chip Thickness | Fig.2 | | |
| 6. Emission Area | Fig.2 | | |

2) Electro-Optical Characteristics [Ta=25°C]

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.9	2.3	V
Reverse Current	Ir	Vr=5V			10	uA
Brightness	Iv	If=20mA	40	60		mcd
Power Intensity	Po	If=20mA	1.5	2.5		mW
Peak Wavelength	λP	If=20mA	650	660	670	nm
Spectral Radiation Bandwidth	Δλ	If=20mA		20		nm
RiseTime	tr	If=20mA		100		ns
FallTime	tf	If=20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit : um]

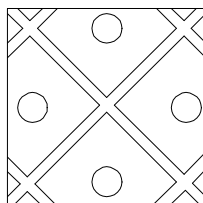
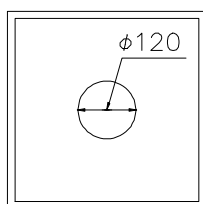


Fig.1 Electrode Pattern

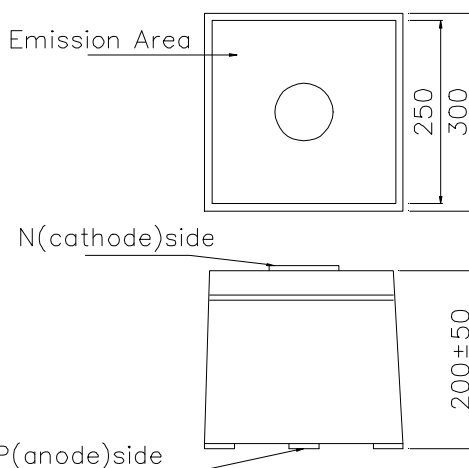


Fig.2 Chip size and Emission Area